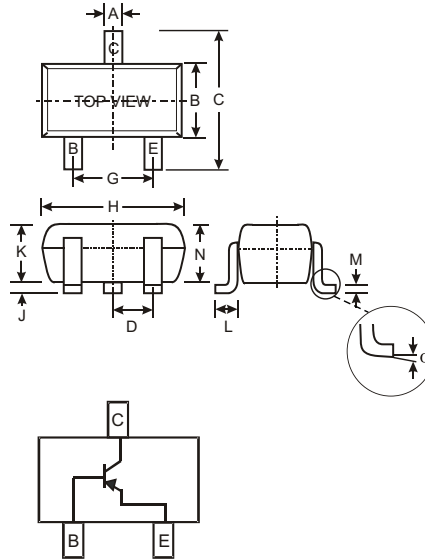


Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT4401T)
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-523, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking (See Page 2): 2T
- Ordering & Date Code Information: See Page 2
- Weight: 0.002 grams (approx.)



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	MMBT4403T	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I _C	-600	mA
Power Dissipation (Note 1)	P _d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

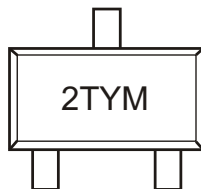
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	-100	nA	$V_{CE} = -35\text{V}, V_{EB(OFF)} = -0.4\text{V}$
Base Cutoff Current	I_{BL}	—	-100	nA	$V_{CE} = -35\text{V}, V_{EB(OFF)} = -0.4\text{V}$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	30 60 100 100 20	— — — 300 —	—	$I_C = -100\mu\text{A}, V_{CE} = -1.0\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -150\text{mA}, V_{CE} = -2.0\text{V}$ $I_C = -500\text{mA}, V_{CE} = -2.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.40 -0.75	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.75 —	-0.95 -1.30	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	8.5	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{eb}	—	30	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1.5	15	k Ω	$V_{CE} = -10\text{V}, I_C = -1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	8.0	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	60	500	—	
Output Admittance	h_{oe}	1.0	100	μS	
Current Gain-Bandwidth Product	f_T	200	—	MHz	$V_{CE} = -10\text{V}, I_C = -20\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, V_{BE(off)} = -2.0\text{V}, I_{B1} = -15\text{mA}$
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$
Fall Time	t_f	—	30	ns	

Ordering Information (Note 3)

Device	Packaging	Shipping
MMBT4403T-7	SOT-523	3000/Tape & Reel

- Note: 2. Short duration pulse test used to minimize self-heating effect.
3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



2T = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: N = 2002)
M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D